

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: 2814 Examiner: Mai, Anh D.

Serial No. 10/036,303 Filed: December 28, 2001

In re Application of: Hawley, et al.

For: METHOD FOR FABRICATING A MOS TRANSISTOR HAVING IMPROVED TOTAL RADIATION-INDUCED LEAKAGE CURRENT

*107/03*

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I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as First Class Mail, in an envelope addressed to Commissioner for Patents, Box AF, Washington, D.C. 20231,  
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Martha N. Griffin

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Box AF  
Director of Patents  
Washington, D.C. 20231

Sir:

In reply to the Office Action mailed on December 26, 2002, Applicant respectfully requests reconsideration of the present rejections and reexamination of the present application in view of the following remarks.

**REMARKS IN REGARD TO OBJECTIONS TO DRAWINGS**

The Examiner has objected to the drawings under 37 C.F.R. 1.83(a) as not showing every feature of the invention specified in the claims. Specifically, the Examiner states that the drawings do not show a "single isolation trench having a uniform cross section." As set forth in the Declaration of Frank Hawley, dated March 25, 2003, enclosed herewith, the drawings *do show* a single isolation trench having a uniform cross section to one of ordinary skill in the art.

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